



## IGBT Discrete

$V_{CE}$	<b>1200</b>	<b>V</b>
$I_C$	<b>15</b>	<b>A</b>
$V_{CE(SAT)} I_C=15A$	<b>1.85</b>	<b>V</b>

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## Features

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## Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	$V_{CE}$	1200	V
DC Collector Current, limited by $T_{jmax}$ $T_C=25^\circ C$ $T_C=100^\circ C$	$I_C$	30 15	A
Diode Forward Current, limited by $T_{jmax}$ $T_C=25^\circ C$ $T_C=100^\circ C$	$I_F$	30 15	A
Continuous Gate-Emitter Voltage	$V_{GE}$	20	V
Transient Gate-Emitter Voltage	$V_{GE}$	30	V
Turn off Safe Operating Area $V_{CE} 1200V$ , $T_j 150^\circ C$		60	A
Pulsed Collector Current, $V_{GE}=15V$ , $t_p$ limited by $T_{jmax}$	$I_{CM}$	60	A
Diode Pulsed Current, $t_p$ limited by $T_{jmax}$	$I_{Fpuls}$	60	A
Short Circuit Withstand Time, $V_{GE}=15V$ , $V_{CC}=900V$ , $V_{CEM} 1200V$	$T_{sc}$	10	$\mu s$
Power Dissipation, $T_j=175^\circ C, T_C=25^\circ C$	$P_{tot}$	200	W



Operating Junction Temperature	$T_j$	-40...+175	°C
Storage Temperature	$T_s$	-55...+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

## Electrical Characteristics of the IGBT $T_j=25$ unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Collector-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE}=0V, I_C=250\mu A$	1200		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA$	5.1	5.8	6.4	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=15A$ $T_j=25^\circ C,$ $T_j=125^\circ C$ $T_j=150^\circ C$		1.85 2.20 2.30	2.35	V
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ C,$ $T_j=150^\circ C$			0.25 5.00	mA
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE}=0V, V_{GE}=\pm 20V$			100	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic</b>						
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	-	1.2	-	nF
Reverse Transfer Capacitance	$C_{res}$		-	0.04	-	
Gate Charge	$Q_G$	$V_{CC}=960V, I_C=15A,$ $V_{GE}=15V$	-	0.14	-	uC
Short Circuit Collector Current	$I_{SC}$	$V_{GE}=15V, t_{sc} 10\mu s,$ $V_{CC}=900V, T_j 150^\circ C$	-	60	-	A



## Electrical Characteristics of the Diode $T_j = 25$ unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Diode Forward Voltage	$V_F$	$I_F = 15A$ $T_j = 25^\circ C$ , $T_j = 125^\circ C$ $T_j = 150^\circ C$		2.00 1.80 1.70	2.40	V

## Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic , at <math>T_j = 25</math></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 15A,$ $V_{GE} = -15V \sim 15V,$ $R_g = 33$	-	45	-	ns
Rise Time	$t_r$		-	52	-	ns
Turn-on Energy	$E_{on}$		-	1.5	-	mJ
Turn-off Delay Time	$t_{d(off)}$		-	128	-	ns
Fall Time	$t_f$		-	186	-	ns
Turn-off Energy	$E_{off}$		-	0.9	-	mJ
<b>Dynamic , at <math>T_j = 125</math></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 15A,$ $V_{GE} = -15V \sim 15V,$ $R_g = 33$	-	50	-	ns
Rise Time	$t_r$		-	55	-	ns
Turn-on Energy	$E_{on}$		-	2.2	-	mJ
Turn-off Delay Time	$t_{d(off)}$		-	160	-	ns
Fall Time	$t_f$		-	135	-	ns
Turn-off Energy	$E_{off}$		-	1.3	-	mJ
<b>Dynamic , at <math>T_j = 150</math></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 15A,$ $V_{GE} = -15V \sim 15V,$ $R_g = 33$	-	52	-	ns
Rise Time	$t_r$		-	58	-	ns
Turn-on Energy	$E_{on}$		-	2.4	-	mJ
Turn-off Delay Time	$t_{d(off)}$		-	170	-	ns
Fall Time	$t_f$		-	138	-	ns
Turn-off Energy	$E_{off}$		-	1.45	-	mJ

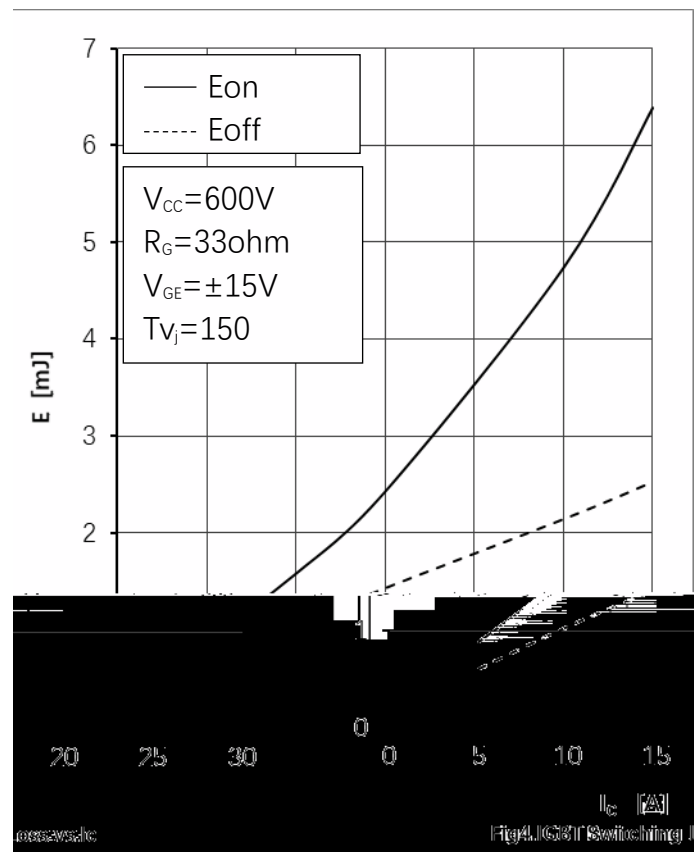
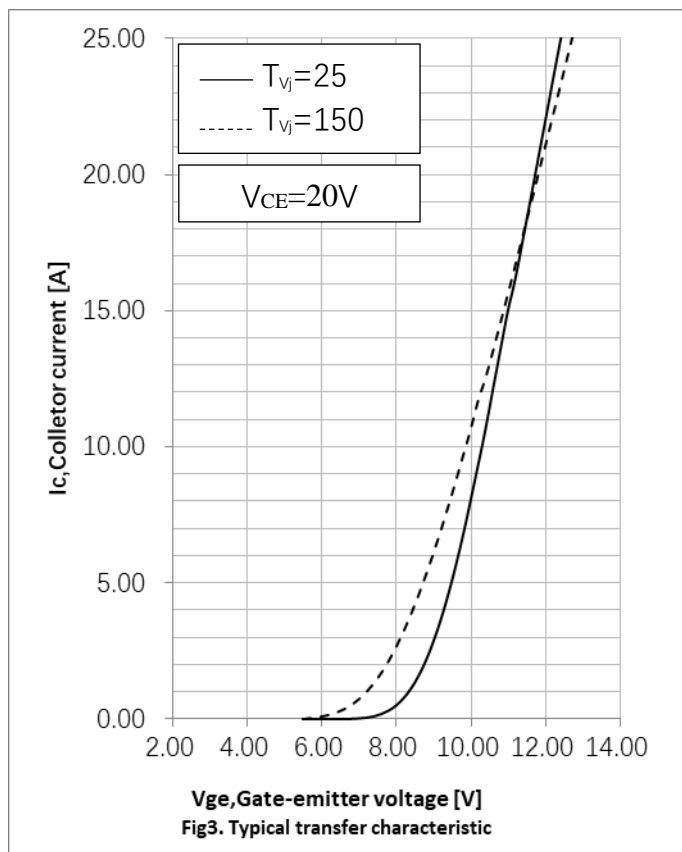
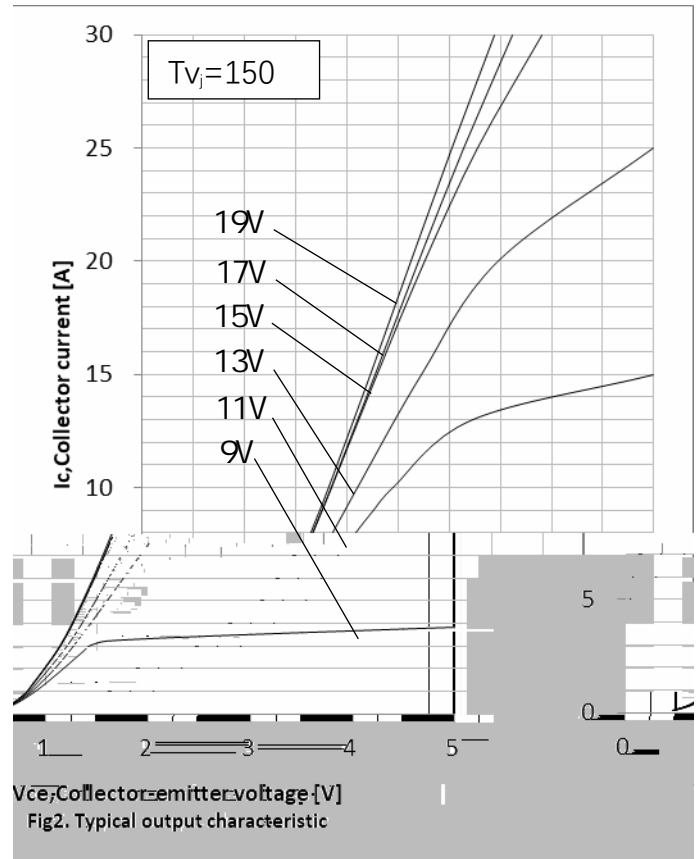
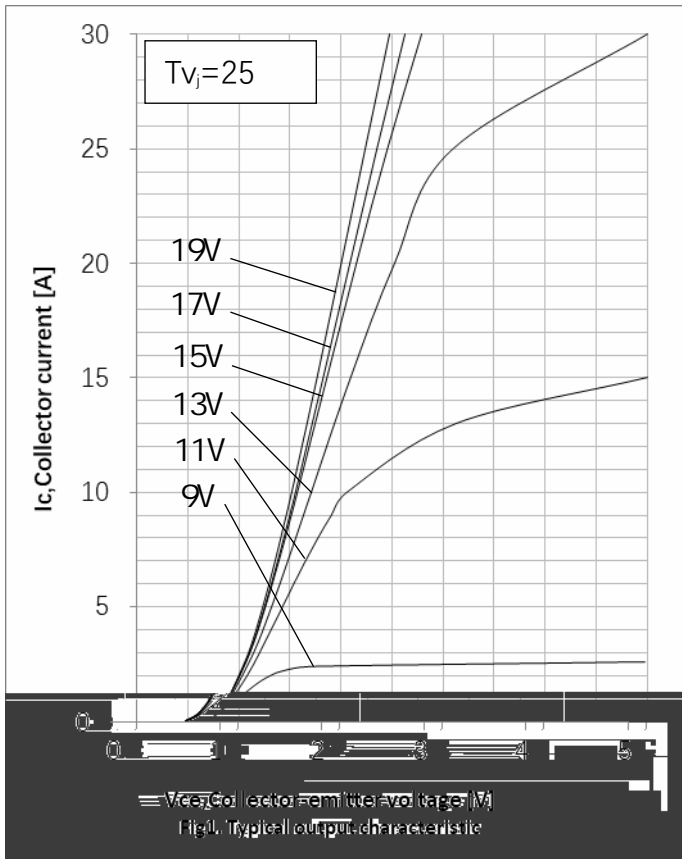


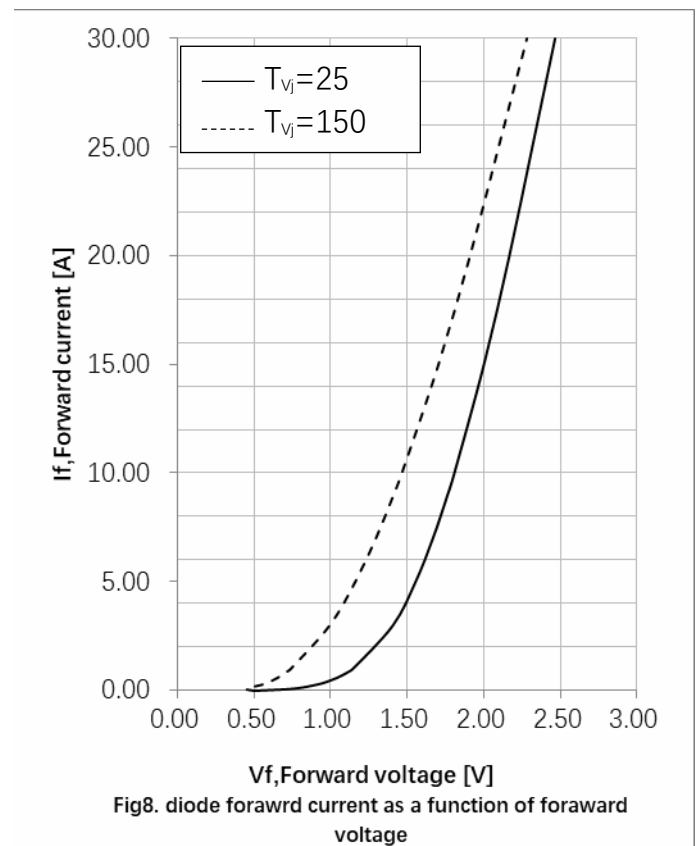
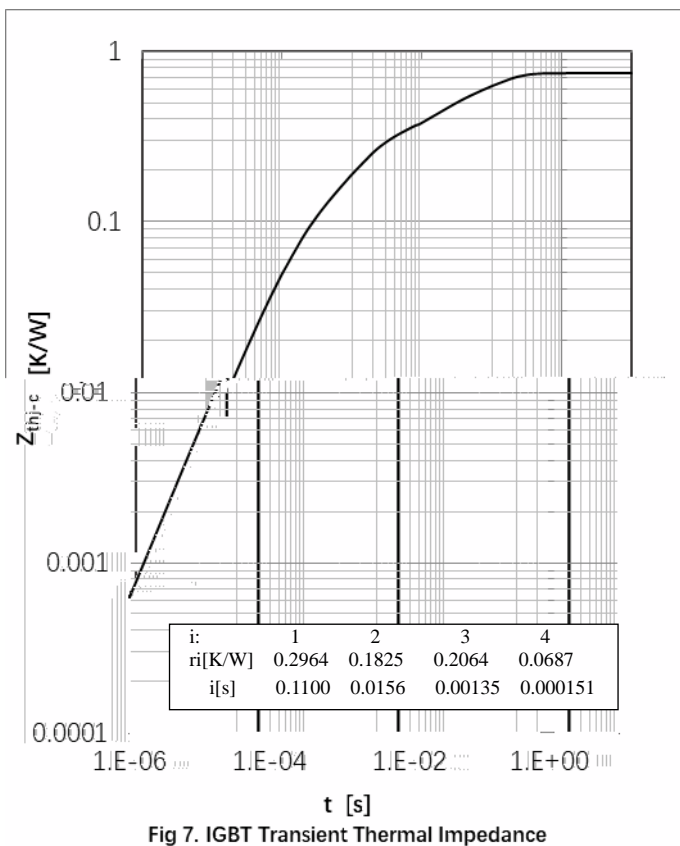
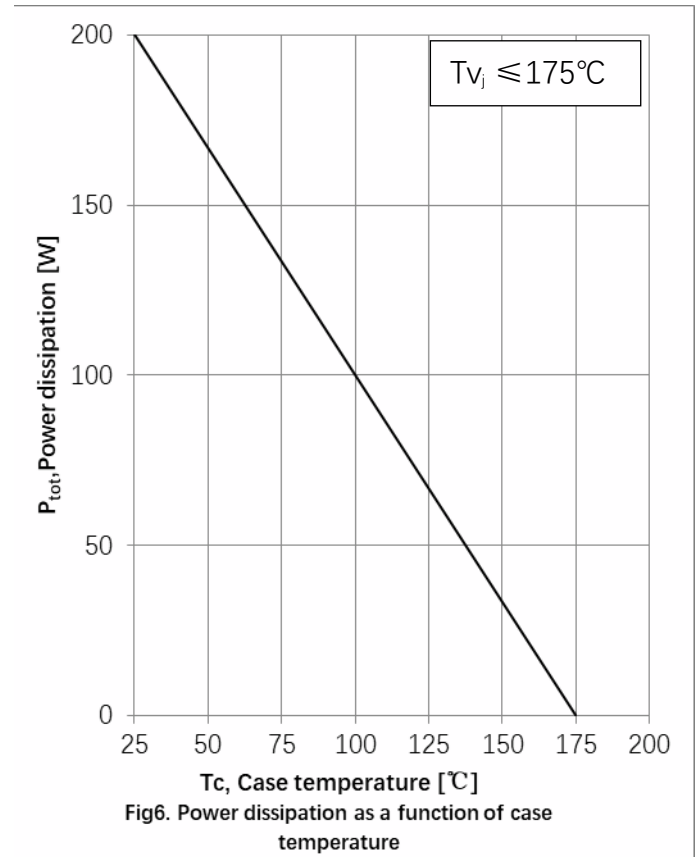
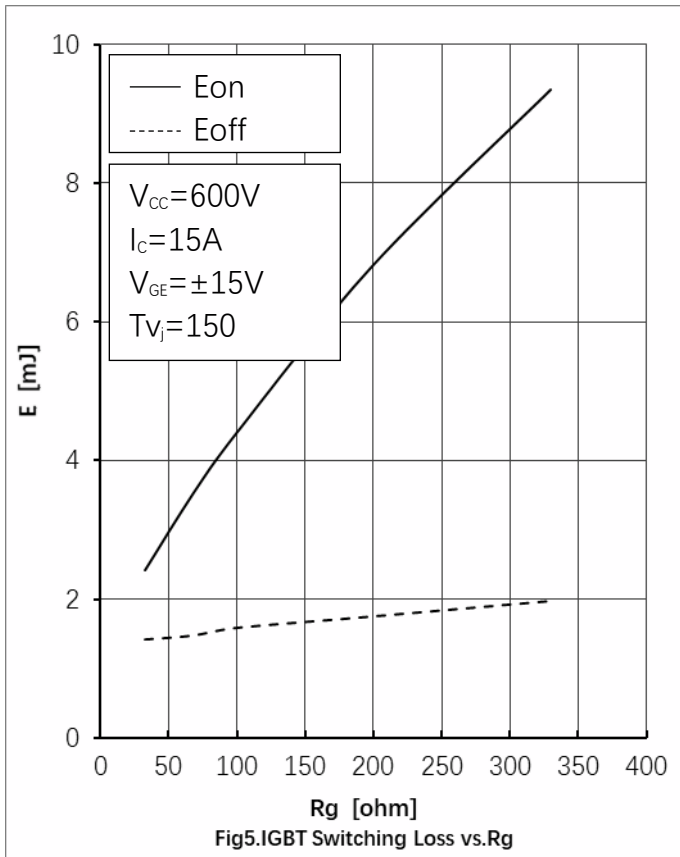
## Electrical Characteristics of the DIODE

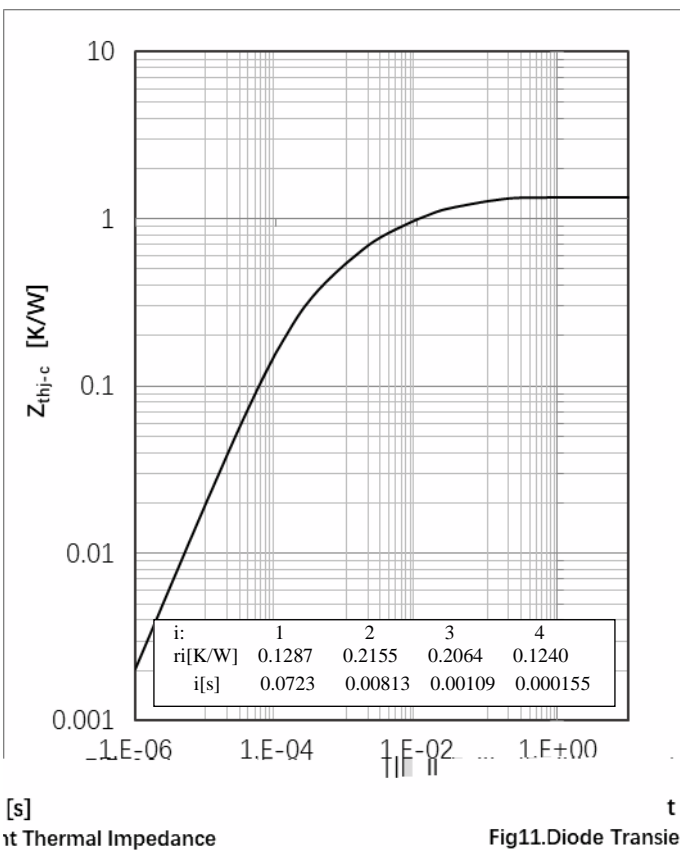
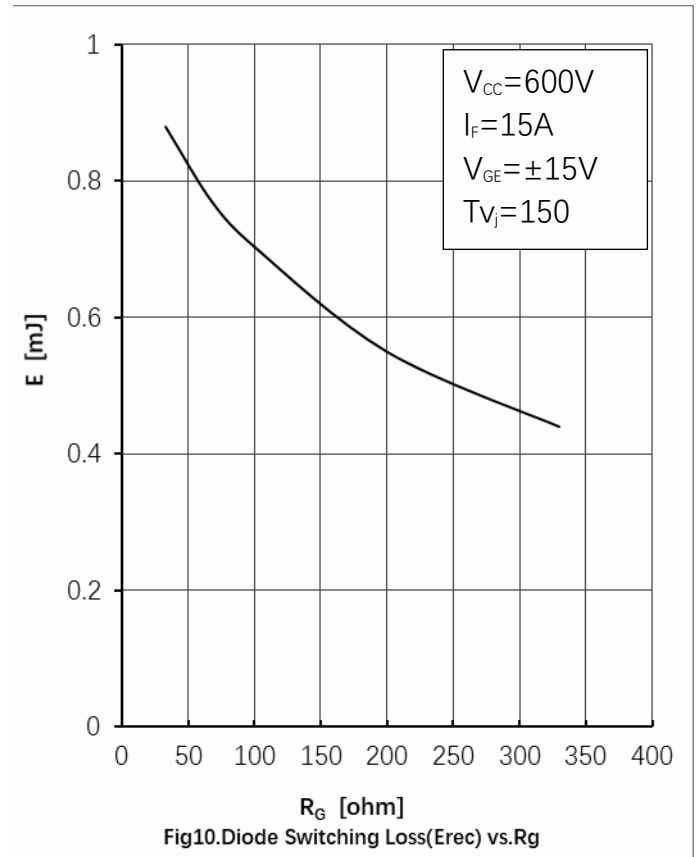
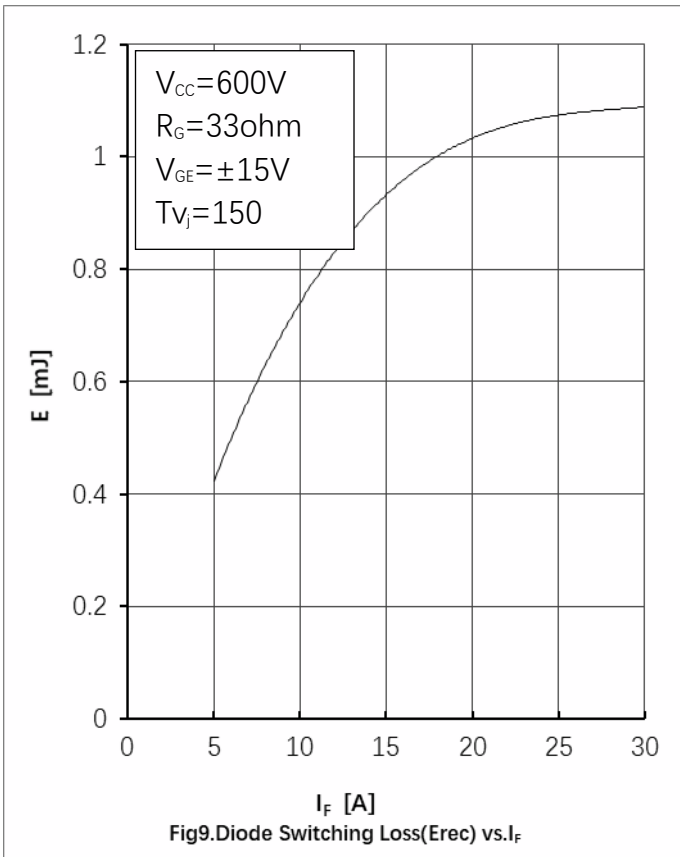
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic , at T<sub>j</sub>= 25</b>						
Diode Forward Voltage	V <sub>FM</sub>	I <sub>F</sub> = 15A	-	1.90	-	V
Reverse Recovery Current	I <sub>rr</sub>	I <sub>F</sub> =15A, V <sub>R</sub> =600V, -di/dt=240A/μs,	-	7.5	-	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	1.8	-	uC
Reverse Recovery Energy	E <sub>rec</sub>		-	0.60		mJ
<b>Dynamic , at T<sub>j</sub>= 125</b>						
Reverse Recovery Current	I <sub>rr</sub>	I <sub>F</sub> =15A, V <sub>R</sub> =600V, -di/dt=240A/μs,	-	9	-	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	2.4	-	uC
Reverse Recovery Energy	E <sub>rec</sub>		-	0.9		mJ
<b>Dynamic , at T<sub>j</sub>= 150</b>						
Reverse Recovery Current	I <sub>rr</sub>	I <sub>F</sub> =15A, V <sub>R</sub> =600V, -di/dt=240A/μs,	-	9.5	-	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	2.6	-	uC
Reverse Recovery Energy	E <sub>rec</sub>		-	1.0		mJ

## Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R <sub>th(j-c)</sub>	0.75	K/W
Diode Thermal Resistance, Junction - Case	R <sub>th(j-c)</sub>	1.35	K/W
Thermal Resistance, Junction - Ambient	R <sub>th(j-a)</sub>	40	K/W

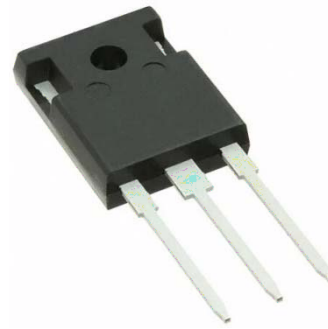
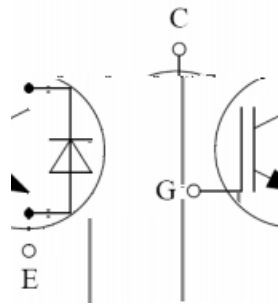






[s]  
t Thermal Impedance

- Circuit Diagram



- Package Outline Information

CASE: TO 247

